Onsemi

N-Channel RF Amplifier

MMBF5484, MMBF5485, **MMBF5486**

This device is designed primarily for electronic switching applications such as low On Resistance analog switching. Sourced from Process 50.

ABSOLUTE MAXIMUM RATINGS* (T_A = 25°C unless otherwise noted)

Symbol	Rating	Value	Unit
V _{DG}	Drain-Gate Voltage	25	V
V _{GS}	Gate-Source Voltage	-25	V
I _{GF}	Forward Gate Current	10	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

*These rating are limiting values above which the serviceability of any semiconductor device may be impaired.

1. These rating are based on a maximum junction temperature of 150°C.

2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

THERMAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

		Мах	
Symbol	Characteristic	*MMBF5484-5486	Unit
P _D	Total Device Dissipation Derate above 25°C	225 1.8	mW mW/°C
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case	-	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient	556	°C/W

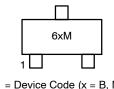
*Device mounted on FR-4 PCB 1.6" x 1.6" x 0.06".



NOTE: Source & Drain are interchangeable

SOT-23 CASE 318-08

MARKING DIAGRAM



6x = Device Code (x = B, M, H) М

= Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBF5484	SOT-23	3000 Tape &
MMBF5484	(Pb-Free)	Reel
MMBF5484		

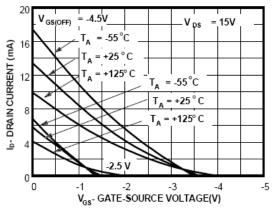
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Symbol	Parameter	Test Condition			Тур	Max	Unit
OFF CHAP	RACTERISTICS	•					
V _{(BR)GSS}	Gate-Source Breakdown Voltage	$I_{G} = -1.0 \ \mu A, \ V_{DS} = 0$		-25	-	-	V
I _{GSS}	Gate Reverse Current	$ \begin{array}{l} V_{GS} = -20 \; V, V_{DS} = 0 \\ V_{GS} = -20 \; V, V_{DS} = 0, T_A = 100^\circ C \end{array} $				-1.0 -0.2	nA μA
V _{GS(off)}	Gate-Source Cutoff Voltage	V _{DS} = 15 V, I _D = 10 nA 5484 5485 5486		-0.3 -0.5 -2.0	- - -	-3.0 -4.0 -6.0	V V V
ON CHAR	ACTERISTICS	•		1	1		
I _{DSS}	Zero-Gate Voltage Drain Current*	V _{DS} = 15 V, V _{GS} = 0	5484 5485 5486	1.0 4.0 8.0	_ _ _	5.0 10 20	mA mA mA
SMALL SI	GNAL CHARACTERISTICS						
9fs	Forward Transfer Conductance	V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz	5484 5485 5486	3000 3500 4000	- - -	6000 7000 8000	μmhos μmhos μmhos
Re _(yis) Input Conductance	Input Conductance	V_{DS} = 15 V, V_{GS} = 0, f = 100 MHz	5484	-	-	100	μmhos
	V_{DS} = 15 V, V_{GS} = 0, f = 400 kHz	5485 / 5486	-	-	1000	μmhos	
g _{os}	Output Conductance	V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz	5484 5485 5486	- - -	- - -	50 60 75	μmhos μmhos μmhos
Re ₍ y _{os)}	Output Conductance	V _{DS} = 15 V, V _{GS} = 0, f = 100 MHz	5484	-	_	75	μmhos
		V_{DS} = 15 V, V_{GS} = 0, f = 400 MHz	5485 / 5486	-	-	100	μmhos
Re ₍ y _{fs)}	Forward Transconductance	V_{DS} = 15 V, V_{GS} = 0, f = 100 MHz	5484	2500	_	-	μmhos
		V_{DS} = 15 V, V_{GS} = 0, f = 400 MHz	5485 5486	3000 3500			μmhos μmhos
C _{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0, f = 1.0 MHz		-	-	5.0	pF
C _{rss}	Reverse Transfer Capacitance	V_{DS} = 15 V, V_{GS} = 0, f = 1.0 MHz		-	-	1.0	pF
C _{oss}	Output Capacitance	V _{DS} = 15 V, V _{GS} = 0, f = 1.0 MHz		-	-	2.0	pF
NF	Noise Figure	V_{DS} = 15 V, R_G = 1.0 k Ω , f = 100 MHz	5484	-	-	3.0	dB
		V_{DS} = 15 V, R_{G} = 1.0 kΩ, f = 400 MHz	5484	-	4.0	-	dB
		V_{DS} = 15 V, R_G = 1.0 kΩ, f = 100 MHz	5485 / 5486	-	_	2.0	dB
		V_{DS} = 15 V, R_G = 1.0 k Ω , f = 400 MHz	5485 / 5486	-	-	4.0	dB

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS





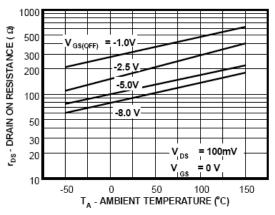


Figure 2. Channel Resistance vs. Temperature

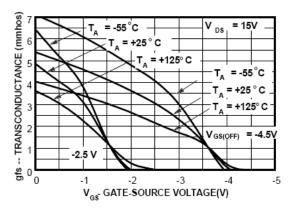


Figure 3. Transconductance Characteristics

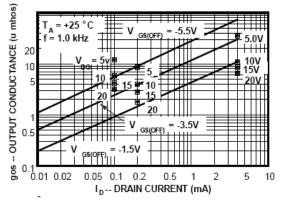


Figure 5. Output Conductance vs. Drain Current

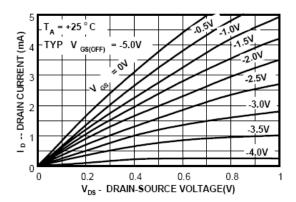


Figure 4. Common Drain–Source Characteristics

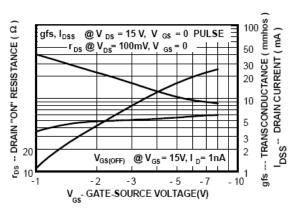


Figure 6. Transconductance Parameter Interactions

TYPICAL CHARACTERISTICS (continued)

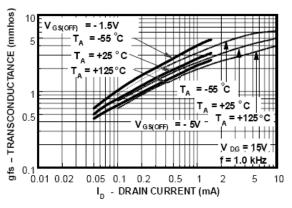


Figure 7. Transconductance vs. Drain Current

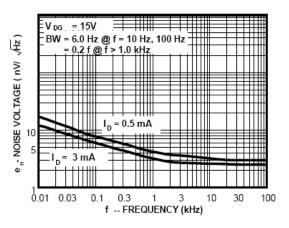


Figure 8. Noise Voltage vs. Frequency

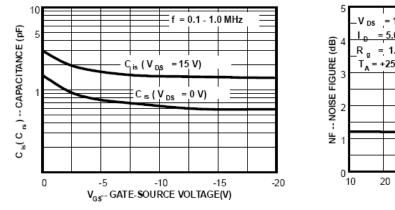


Figure 9. Capacitance vs. Voltage

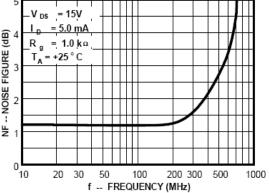


Figure 10. Noise Figure Frequency

COMMON SOURCE CHARACTERISTICS

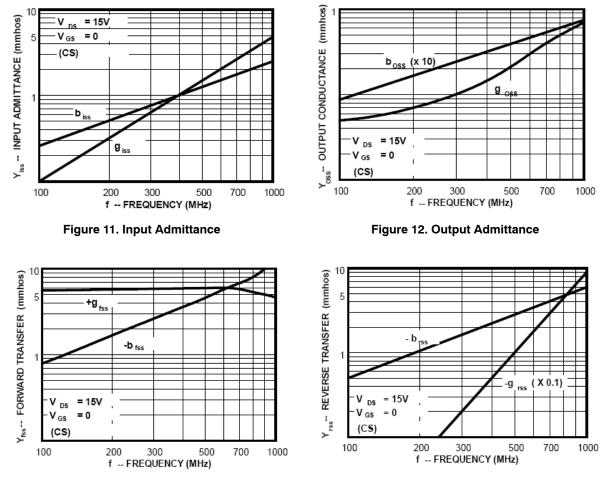
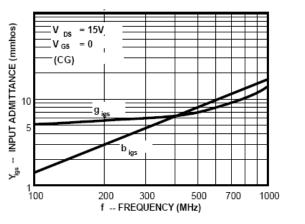


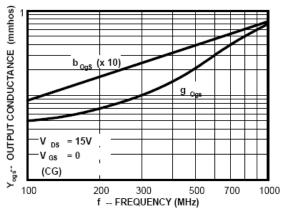
Figure 13. Forward Transadmittance

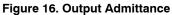
Figure 14. Reverse Transadmittance

COMMON GATE CHARACTERISTICS









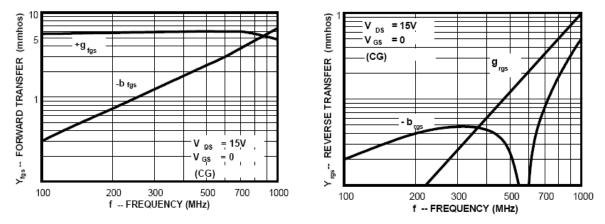
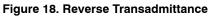


Figure 17. Forward Transadmittance



MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

D

3

TOP VIEW

SIDE VIEW

Нe

-3X b



SCALE 4:1

A____ ' A1SOT-23 (TO-236) CASE 318 ISSUE AT

0.25

-L1

DETAIL A

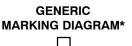
END VIEW

DATE 01 MAR 2023

NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
с	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
Η _E	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10*	0*		10*



DETAIL A



- XXX = Specific Device Code
- M = Date Code
- = Pb–Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

onsemi

SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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